

# PUMD24

# 50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$

31 March 2023

Product data sheet

## 1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: PUMB24 NPN/NPN complement: PUMH24

#### 2. Features and benefits

- Built-in bias resistors
- · Simplifies circuit design
- Reduces component count
- · Reduces pick and place costs
- AEC-Q101 qualified

# 3. Applications

- Low current peripheral driver
- · Control of IC inputs
- · Replacement of general-purpose transistors in digital applications

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	er transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	=	20	mA
R1	bias resistor 1 (input)		[2]	70	100	130	kΩ
R2/R1	bias resistor ratio	T <sub>amb</sub> = 25 °C	[2]	0.8	1	1.2	

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 75 74	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	O1	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	GND1 I1 O2
				006aaa143

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package		
	Name	Description	Version
PUMD24		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>

# 7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD24	T8%

[1] % = placeholder for manufacturing site code

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

# 8. Limiting values

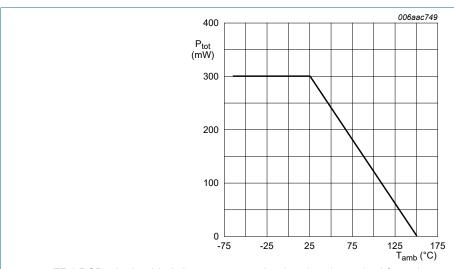
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or			•		
V <sub>CBO</sub>	collector-base voltage	open emitter	[1]	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	[1]	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	[1]	-	10	V
VI	input voltage	input voltage TR1		-10	40	V
		input voltage TR2		-40	10	V
Io	output current		[1]	-	20	mA
I <sub>CM</sub>	peak collector current		[1]	-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	200	mW
Per device	'		,	1		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> For the PNP transistor with negative polarity.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35  $\mu m$  copper, tin-plated and standard footprint

Fig. 1. Per device: Power derating curve

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

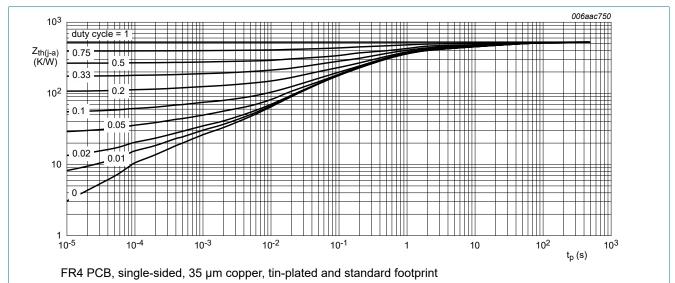


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

# 10. Characteristics

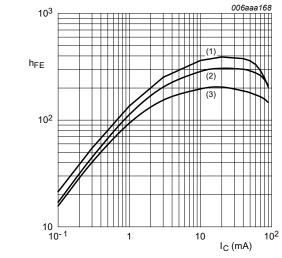
**Table 7. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	50	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	100	nA
OLO	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	100	nA
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C	[1]	-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	50	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 20 mA; T <sub>amb</sub> = 25 °C	[1]	80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	150	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C	[1]	-	1.1	0.5	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 1 mA; T <sub>amb</sub> = 25 °C	[1]	3	1.5	-	V
R1	bias resistor 1 (input)		[2]	70	100	130	kΩ
R2/R1	bias resistor ratio	T <sub>amb</sub> = 25 °C	[2]	0.8	1	1.2	
TR1 (NPN)						_	
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	-	2.5	pF
TR2 (PNP)							
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	-	3	pF

<sup>[1]</sup> For the PNP transistor with negative polarity.

<sup>[2]</sup> See section "Test information" for resistor calculation and test conditions.

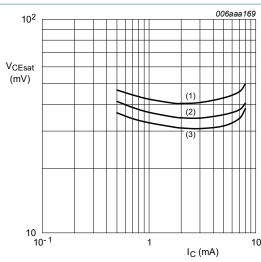
#### 50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$



 $V_{CE} = 5 V$ (1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

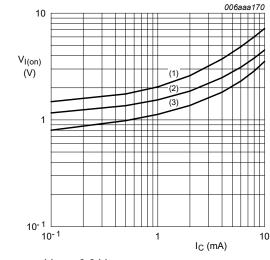
TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$ 

(1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



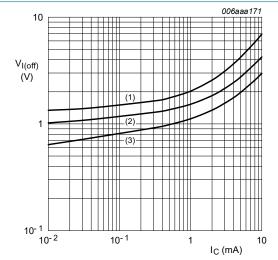
 $V_{CE}$  = 0.3 V

(1) T<sub>amb</sub> = -40 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 





 $V_{CE} = 5 V$ 

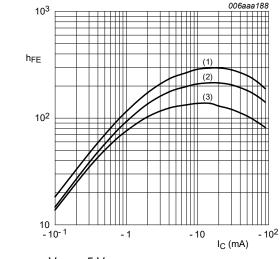
(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

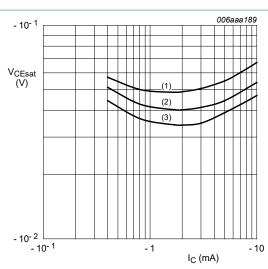
#### 50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$



V<sub>CE</sub> = -5 V

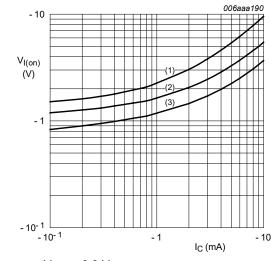
(1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

TR2 (PNP): DC current gain as a function of Fig. 7. collector current; typical values



 $I_{C}/I_{B} = 20$ (1)  $T_{amb} = 100 \, ^{\circ}C$ (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 8. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



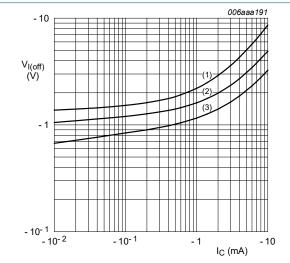
 $V_{CE} = -0.3 \text{ V}$ 

(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2) T<sub>amb</sub> = 25 °C

(3) T<sub>amb</sub> = 100 °C





 $V_{CE}$  = -5 V

(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

TR2 (PNP): On-state input voltage as a function | Fig. 10. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

#### 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

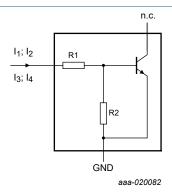


Fig. 11. TR1 (NPN): Resistor test circuit

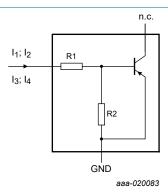


Fig. 12. TR2 (PNP): Resistor test circuit

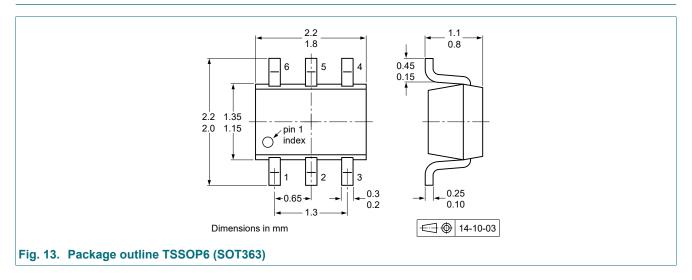
#### **Resistor test conditions**

**Table 8. Resistor test conditions** 

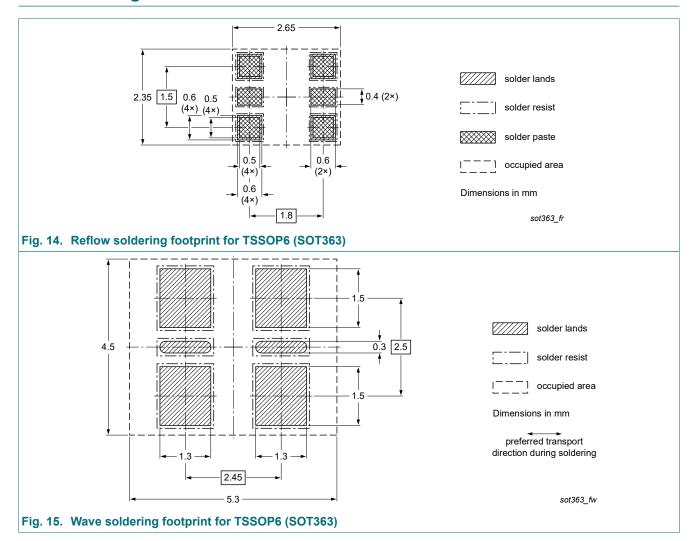
PUMD24	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	14
TR1 (NPN)	100	100	20 μΑ	60 μΑ	-20 μA	-40 μA
TR2 (PNP)	100	100	-20 μA	-60 μΑ	20 μΑ	40 μA

50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 kΩ, R2 = 100 kΩ

# 12. Package outline



# 13. Soldering



50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$ 

# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD24 v.2	20230331	Product data sheet	-	PEMD24_PUMD24_1
Modifications:	Nexperia. • Legal texts have bee	ta sheet has been redesion adapted to the new conduced to single type data removed.	mpany name where appro	, 0
PEMD24_PUMD24_1	20050502	Product data sheet	-	-

#### 50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PUMD24

## 50 V, 20 mA NPN/PNP resistor-equipped double transistor; R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 31 March 2023

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